

# YJGD40N03B

---

**YJGD40N03B**

---



## Typical Electrical and Thermal Characteristics Diagrams

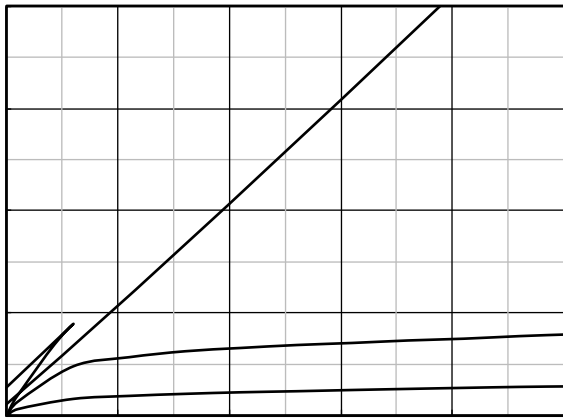


Figure 1. Output Characteristics

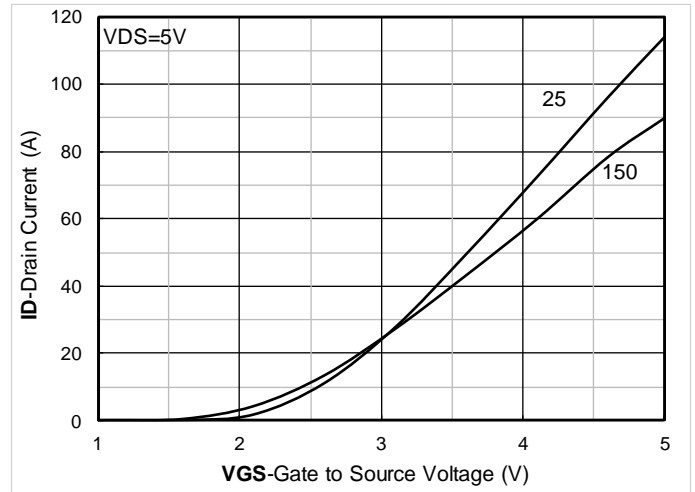


Figure 2. Transfer Characteristics

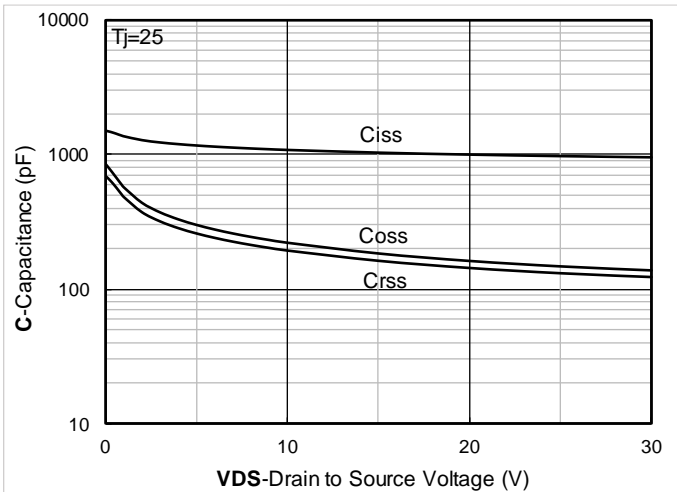


Figure 3. Capacitance Characteristics

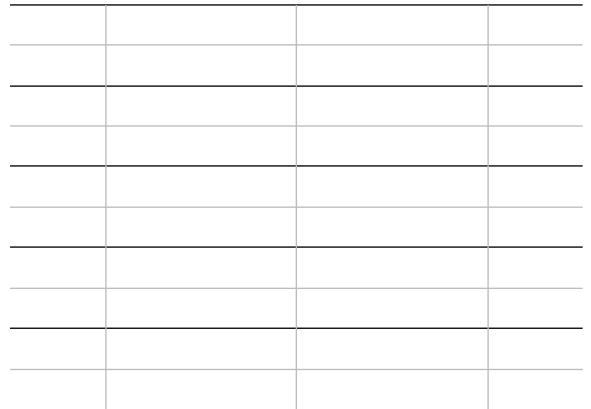


Figure 4. Gate Charge

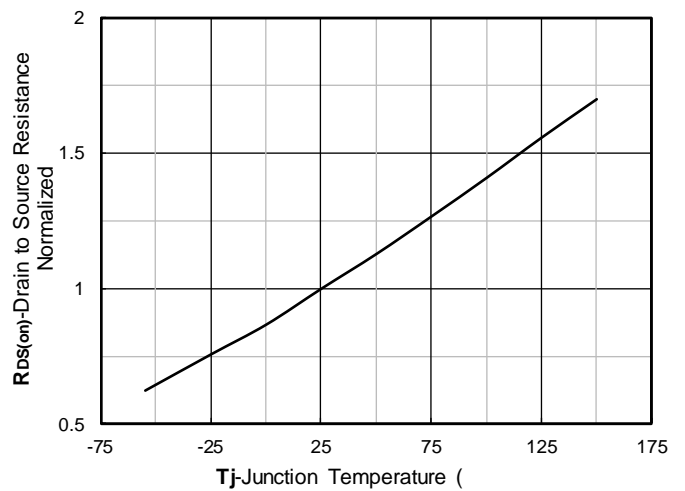


Figure 5. On-Resistance vs Gate to Source Voltage

Figure 6. Normalized On-Resistance

**YJGD40N03B**

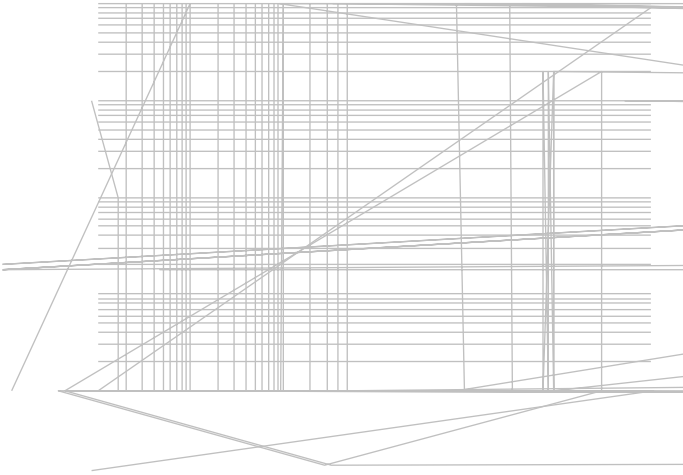


Figure 13. Maximum Transient Thermal Impedance

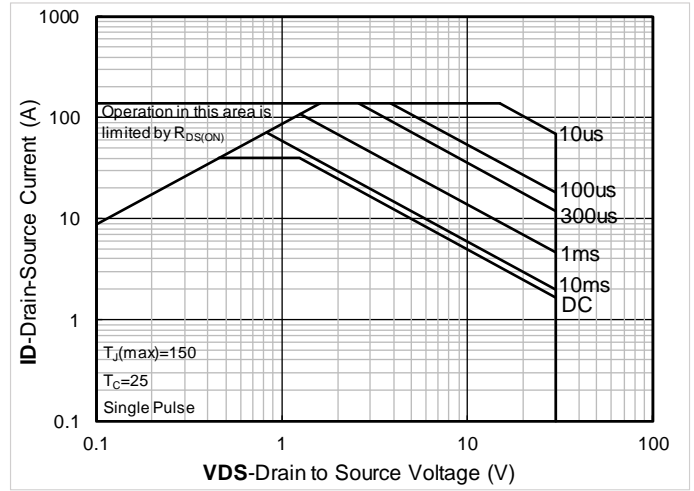


Figure 14. Safe Operation Area

## Test Circuits & Waveforms

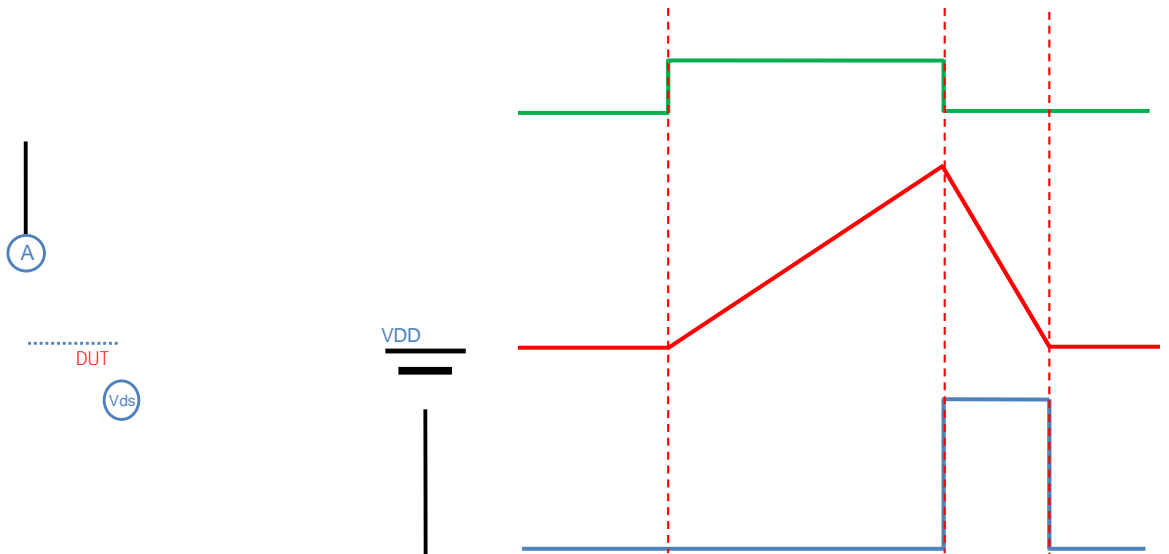


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform



Figure B. Gate Charge Test Circuit & Waveform

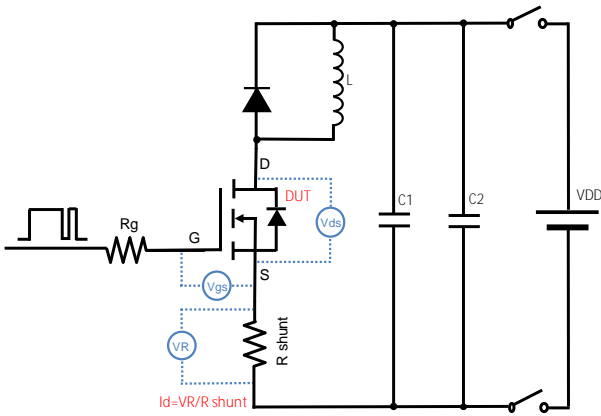


Figure C. Resistive Switching Test Circuit & Waveform

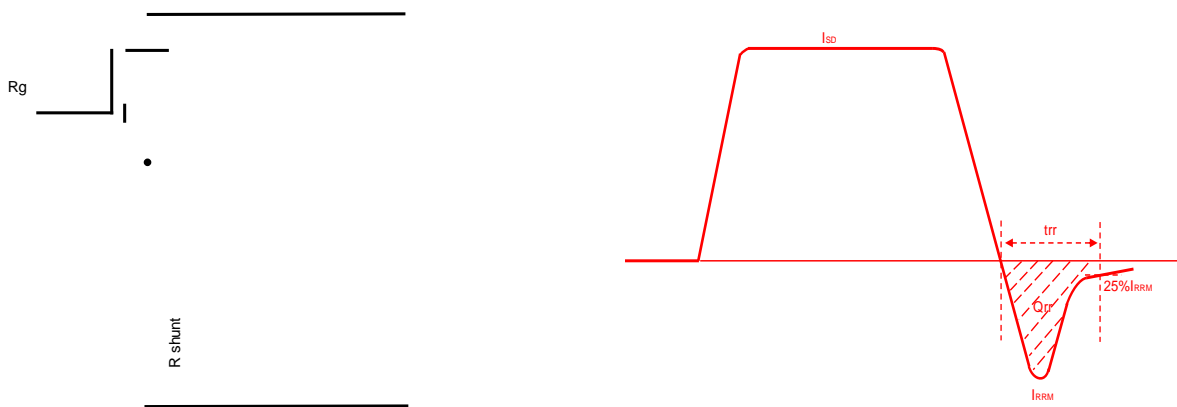
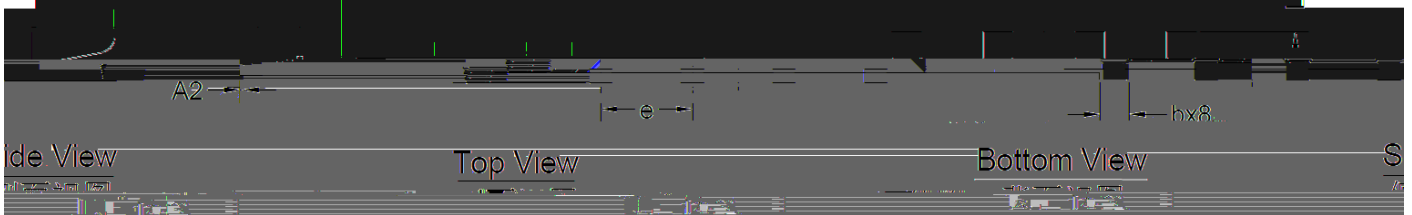
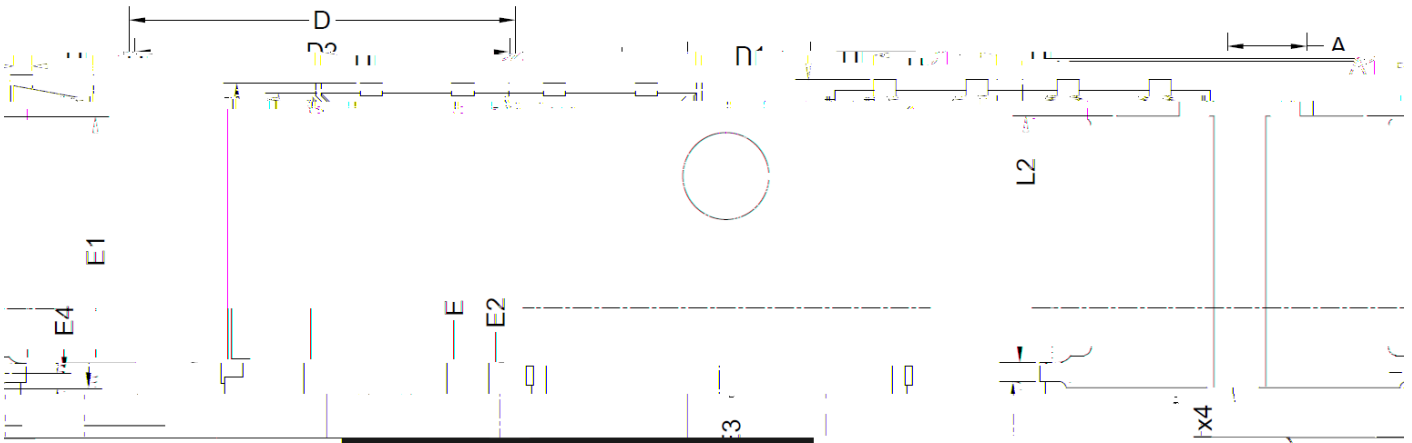


Figure D. Diode Recovery Test Circuit & Waveform



# YJGD40N03B

## PDFN5060-8L-E-1.1mm Package information



A	1.00	1.10	1.20	0.500
A1	0.254 BSC			
A2			0.10	
D1	1.50	1.70	1.90	
E1	3.52	3.72	3.92	3.968
E2	5.66	5.86	6.06	6.250
E3	0.254 REF			
E4	0.21 REF			
L2	1.10	0.95 REF	0.76 REF	
L3	1.20	0.50 BSC		
L4	1.27 BSC			
L5	1.10	0.95 REF	0.76 REF	
L6	1.20	0.50 BSC		
L7	1.27 BSC			
L8	1.10	0.95 REF	0.76 REF	
L9	1.20	0.50 BSC		
L10	1.27 BSC			



## YJGD40N03B

---

### Disclaimer

The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-